

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

SFT1446 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1=39m Ω (typ)
- · 4V drive

- Input Capacitance Ciss=750pF(typ)
- · Halogen free compliance

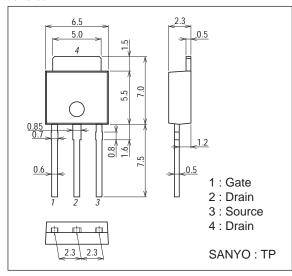
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		60	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		20	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	80	А
Allowable Power Dissipation	D-		1	W
	PD	Tc=25°C	23	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

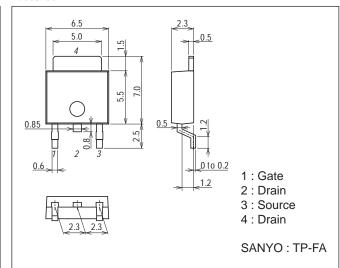
Package Dimensions

unit : mm (typ) 7518-004



Package Dimensions

unit : mm (typ) 7003-004



Product & Package Information

• Package : TP

• JEITA, JEDEC: SC-64, TO-251, SOT553

• Minimum Packing Quantity: 500 pcs./bag

Marking(TP, TP-FA)



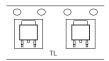
Product & Package Information

• Package : TP-FA

• JEITA, JEDEC : SC-63, TO-252, SOT428

• Minimum Packing Quantity: 700 pcs./reel

Taping Type(TP-FA) : TL



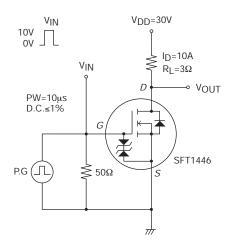
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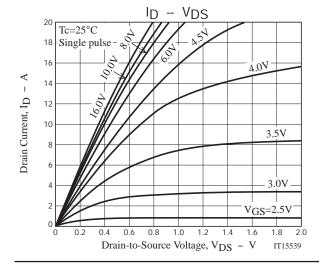
http://semicon.sanyo.com/en/network

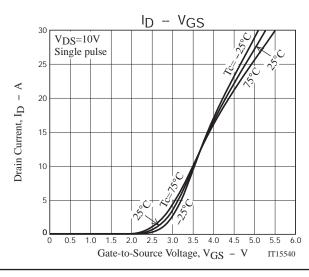
Electrical Characteristics at Ta=25°C

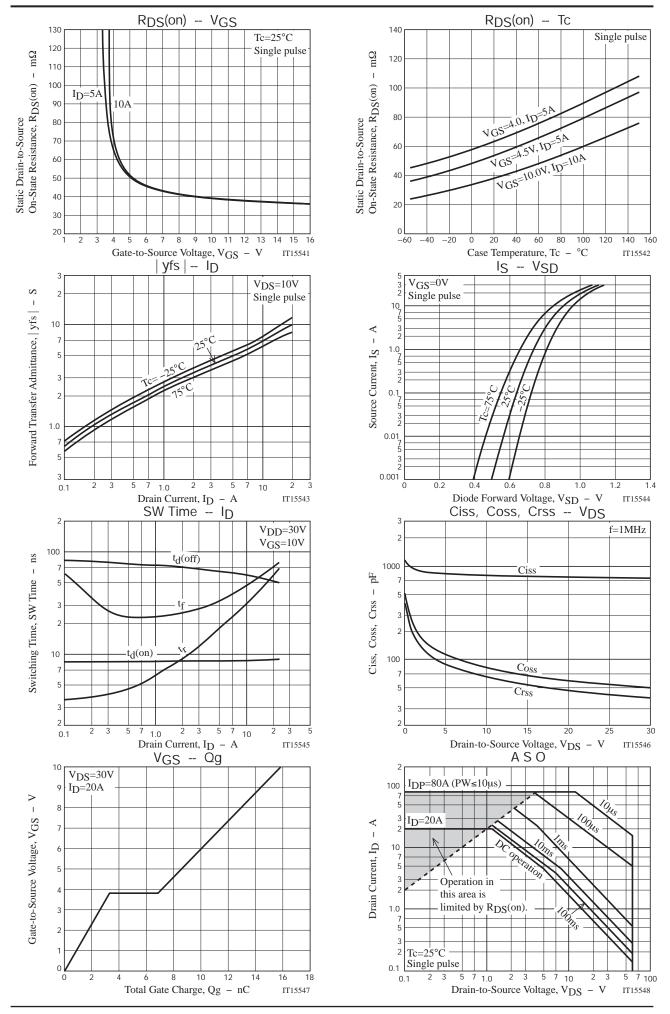
Parameter	Symbol	Conditions	Ratings			1.1-24
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	60			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =60V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=10A		7.0		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =10A, V _{GS} =10V		39	51	mΩ
	R _{DS} (on)2	I _D =5A, V _G S=4.5V		54	76	mΩ
	R _{DS} (on)3	I _D =5A, V _{GS} =4V		62	87	mΩ
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		750		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		59		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		47		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		8.5		ns
Rise Time	tr	See specified Test Circuit.		31		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		60		ns
Fall Time	tf	See specified Test Circuit.		48		ns
Total Gate Charge	Qg	V _{DS} =30V, V _{GS} =10V, I _D =14A		16		nC
Gate-to-Source Charge	Qgs	V _{DS} =30V, V _{GS} =10V, I _D =14A		3.3		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =30V, V _{GS} =10V, I _D =14A		3.6		nC
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V		1.01	1.2	V

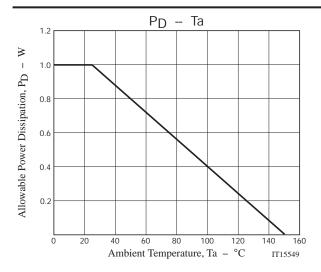
Switching Time Test Circuit

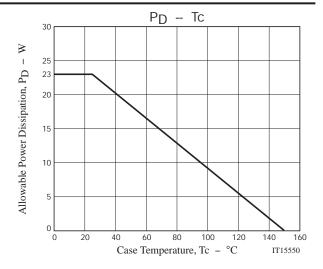












Note on usage: Since the SFT1446 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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